

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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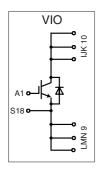


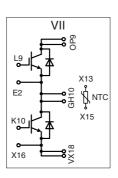


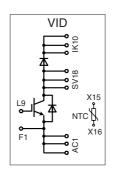
IGBT Modules in ECO-PAC 2

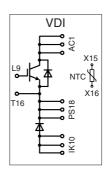
Short Circuit SOA Capability Square RBSOA

Preliminary data sheet









I_{C25} 93 A = 600 V $V_{CE(sat) typ.} = 2.4 V$



Pin arangement see outlines

IGBTs			
Symbol	Conditions	Maximum	Ratings
V _{CES}	$T_{VJ} = 25^{\circ}C$ to $150^{\circ}C$	600	V
V _{GES}		± 20	V
I _{C25} I _{C80}	$T_{C} = 25^{\circ}C$ $T_{C} = 80^{\circ}C$	93 63	A A
I _{CM} V _{CEK}	V_{GE} = ±15 V; R_{G} = 15 Ω; T_{VJ} = 125°C RBSOA, Clamped inductive load; L = 100 μH	150 V _{CES}	А
t _{sc} (SCSOA)	$V_{CE} = V_{CES}; V_{GE} = \pm 15 \text{ V}; R_{G} = 15 \Omega; T_{VJ} = 125 ^{\circ}\text{C}$ non-repetitive	10	μs
P _{tot}	$T_c = 25$ °C	294	W

Symbol	Conditions (T _{vi} = 25°C	Characteristic Values , unless otherwise specified)			
	, vo	min.	typ.	max.	
V _{CE(sat)}	$I_{C} = 100 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.4 2.8	2.8	V V
V _{GE(th)}	$I_{\rm C}$ = 1.5 mA; $V_{\rm GE}$ = $V_{\rm CE}$	4.5		6.5	V
I _{CES}	$V_{CE} = V_{CES}$; $V_{GE} = 0 \text{ V}$; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$			1.4 6.5	mA mA
I _{GES}	$V_{\text{CE}} = 0 \text{ V}; V_{\text{GE}} = \pm 20 \text{ V}$			150	nA
$\begin{aligned} & \mathbf{t}_{\text{d(on)}} \\ & \mathbf{t}_{\text{r}} \\ & \mathbf{t}_{\text{d(off)}} \\ & \mathbf{t}_{\text{f}} \\ & \mathbf{E}_{\text{on}} \\ & \mathbf{E}_{\text{off}} \end{aligned}$	Inductive load, $T_{VJ} = 125^{\circ}C$ $V_{CE} = 300 \text{ V; } I_{C} = 60 \text{ A}$ $V_{GE} = 15/0 \text{ V; } R_{G} = 15 \Omega$		150 60 450 40 3.2 2.2		ns ns ns ns mJ mJ
C _{ies}	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$		4.2		nF
R _{thJC} R _{thJH}	(per IGBT) with heatsink compound (0.42 K/m.K; 50 μm))	0.85	0.43	K/W K/W
IXYS reserv	es the right to change limits, test conditions and	dimensions			

Features

- NPT IGBT's
- positive temperature coefficient of saturation voltage
- fast switching
- FRED diodes
 - fast reverse recovery
 - low forward voltage
- Industry Standard Package
 - solderable pins for PCB mounting
 - isolated DCB ceramic base plate

Advantages

- space and weight savings
- reduced protection circuits
- leads with expansion bend for stress relief

Typical Applications

- AC and DC motor control
- AC servo and robot drives
- power supplies
- · welding inverters

Recommended replacement: Please contact your local sales office



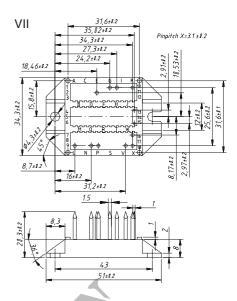
Reverse diodes (FRED)				
Symbol	Conditions	Maximum Ratings		
I _{F25}	$T_{C} = 25^{\circ}C$	134 A		
I _{F80}	$T_C = 80^{\circ}C$	82 A		

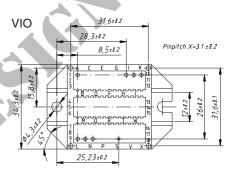
Symbol	Conditions	Cha	Characteristic Values		
		min.	typ.	max.	
V _F	$I_F = 60 \text{ A}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		1.78 1.33	1.99	V
I _{RM}	$\begin{cases} I_{_{F}} = 60 \text{ A; } di_{_{F}}/dt = 500 \text{ A/}\mu\text{s; } T_{_{VJ}} = 125^{\circ}\text{C} \\ V_{_{R}} = 300 \text{ V; } V_{_{GE}} = 0 \text{ V} \end{cases}$		28 100		A ns
${\sf R}_{\sf thJC} \ {\sf R}_{\sf thJH}$	with heatsink compound (0.42 K/m.K; 50 μm)		1.32	0.66	K/W K/W

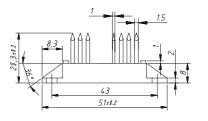
Temperature Sensor NTC					
Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
R ₂₅ B _{25/50}	T = 25°C	4.75	5.0 3375	5.25	kΩ K

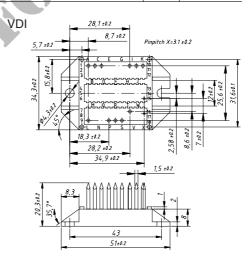
Module			
Symbol	Conditions	Maximum Ratings	
T _{vJ}		-40+150 -40+150	°C °C
V _{ISOL}	I _{ISOL} ≤ 1 mA; 50/60 Hz	3000	V~
M _d	mounting torque (M4)	1.5 - 2.0 14 - 18	Nm lb.in.
а	Max. allowable acceleration	50	m/s²

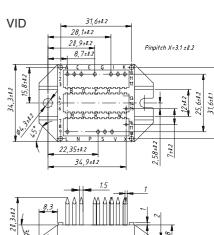
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
d _s d _A	Creepage distance on surface (Pin to heatsink) Strike distance in air (Pin to heatsink)	11.2 11.2		mm mm
Weight			24	g

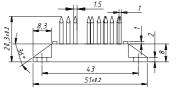












Data according to IEC 60747 and refer to a single transistor or diode unless otherwise stated. IXYS reserves the right to change limits, test conditions and dimensions.

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